DOCUMENT CHANGE REQUEST

DCR number 413
Changes required for: N/A
Date: 2008/06/18
Date sent: 2008/06/18
Status: IMPLEMENTED
Originator: Aissa Nehdi
Organisation: CNES

Title:	Transistors High Voltage NPN, based on type 2N5551		
Number:	5201/019	Issue:	3

Other documents affected:

Page:

2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS
PAGE 14

Paragraph:

2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS
PAGE 14

Original wording:

Proposed wording:

Forward-Current Transfer Ratio 2
Symbols hFE2
TEST LIMIT MIN 80
TEST LIMIT MAX 250

Justification:

Typing error

Attachments:
N/A
Modifications:
N/A
Approval signature:
Date signed:
2008-06-18